

AM4457P3C-F-R Phototransistor

DESCRIPTION

- Made with NPN silicon phototransistor chips

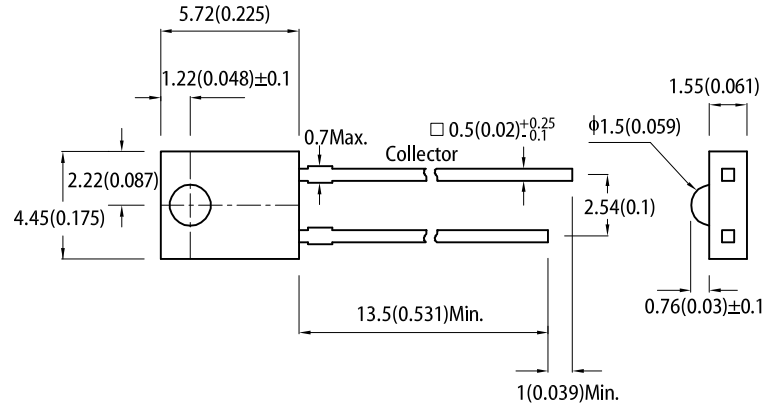
FEATURES

- Mechanically and spectrally matched to infrared emitting LED lamp
- Halogen-free
- Water clear lens
- RoHS compliant

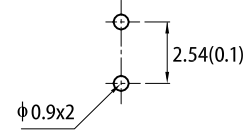
APPLICATIONS

- Infrared applied systems
- Optoelectronic switches
- Photodetector control circuits
- Sensor technology

PACKAGE DIMENSIONS



Recommended PCB Layout



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.
4. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.

ABSOLUTE MAXIMUM RATINGS at $T_A=25^\circ\text{C}$

Parameter	Max.Ratings	Units
Collector-to-Emitter Voltage	30	V
Emitter-to-Collector Voltage	5	V
Power Dissipation at (or below) 25°C Free Air Temperature	100	mW
Operating Temperature	-40 to +85	$^\circ\text{C}$
Storage Temperature	-40 to +85	$^\circ\text{C}$
Lead Soldering Temperature(>5mm for 5sec)	260	$^\circ\text{C}$

Note:

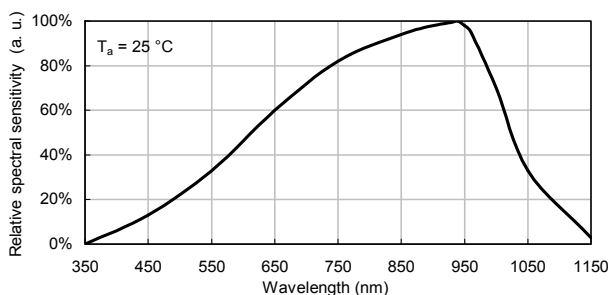
1. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

ELECTRICAL / OPTICAL CHARACTERISTICS at $T_A=25^\circ\text{C}$

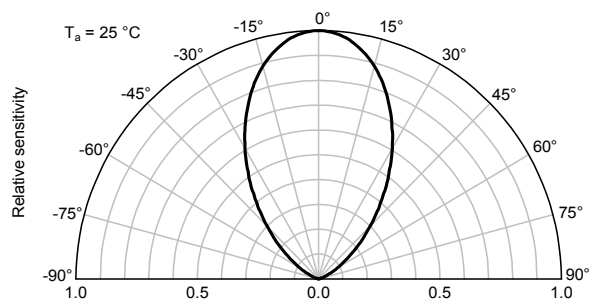
Parameter	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Collector-to-Emitter Breakdown Voltage	$V_{BR\ CE0}$	30	-	-	V	$I_C = 100\mu\text{A}$ $E_e = 0\text{mW}/\text{cm}^2$
Emitter-to-Collector Breakdown Voltage	$V_{BR\ ECO}$	5	-	-	V	$I_E = 100\mu\text{A}$ $E_e = 0\text{mW}/\text{cm}^2$
Collector-to-Emitter Saturation Voltage	$V_{CE(SAT)}$	-	-	0.8	V	$I_C = 2\text{mA}$ $E_e = 20\text{mW}/\text{cm}^2$
Collector Dark Current	I_{CEO}	-	-	100	nA	$V_{CE} = 10\text{V}$ $E_e = 0\text{mW}/\text{cm}^2$
Rise Time(10% to 90%)	T_R	-	15	-	μS	$V_{CE} = 5\text{V}$ $I_C = 1\text{mA}$ $R_L = 1000\Omega$
Fall Time(90% to 10%)	T_F	-	15	-	μS	
On State Collector Current	$I_{(ON)}$	0.35	0.8	-	mA	$V_{CE} = 5\text{V}$ $E_e = 1\text{mW}/\text{cm}^2$ $\lambda = 940\text{nm}$
Range of spectral bandwidth	$\lambda_{0.1}$	420	-	1120	nm	-
Wavelength of peak sensitivity	λ_p	-	940	-	nm	-
Angle of half sensitivity	$2\theta_{1/2}$	-	70	-	deg	-

TECHNICAL DATA

RELATIVE SPECTRAL SENSITIVITY vs. WAVELENGTH

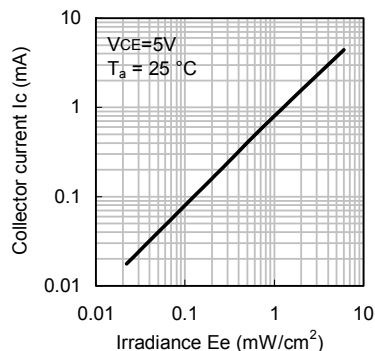


RELATIVE RADIANT SENSITIVITY vs. ANGULAR DISPLACEMENT

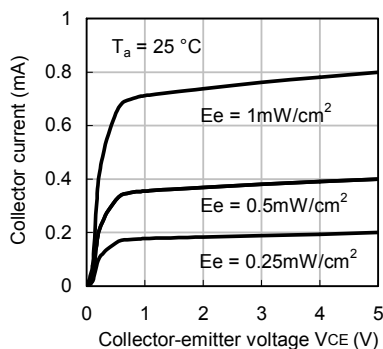


PHOTOTRANSISTOR

Collector Current vs. Irradiance



Collector Current vs. Collector-Emitter Voltage



Relative Collector Current vs. Ambient Temperature

